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### What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, I <sup>2</sup> C, IrDA, LINbus, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I <sup>2</sup> S, POR, PWM, WDT
Number of I/O	53
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.8V
Data Converters	A/D 12bit SAR; D/A 12bit
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TQFP
Supplier Device Package	64-TQFP (10x10)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/silicon-labs/efm32tg11b120f128gq64-ar">https://www.e-xfl.com/product-detail/silicon-labs/efm32tg11b120f128gq64-ar</a>

## 2. Ordering Information

Table 2.1. Ordering Information

Ordering Code	Flash (kB)	RAM (kB)	DC-DC Converter	LCD	GPIO	Package	Temp Range
EFM32TG11B520F128GM80-A	128	32	Yes	Yes	67	QFN80	-40 to +85°C
EFM32TG11B520F128GQ80-A	128	32	Yes	Yes	63	QFP80	-40 to +85°C
EFM32TG11B520F128IM80-A	128	32	Yes	Yes	67	QFN80	-40 to +125°C
EFM32TG11B520F128IQ80-A	128	32	Yes	Yes	63	QFP80	-40 to +125°C
EFM32TG11B540F64GM80-A	64	32	Yes	Yes	67	QFN80	-40 to +85°C
EFM32TG11B540F64GQ80-A	64	32	Yes	Yes	63	QFP80	-40 to +85°C
EFM32TG11B540F64IM80-A	64	32	Yes	Yes	67	QFN80	-40 to +125°C
EFM32TG11B540F64IQ80-A	64	32	Yes	Yes	63	QFP80	-40 to +125°C
EFM32TG11B520F128GM64-A	128	32	Yes	Yes	53	QFN64	-40 to +85°C
EFM32TG11B520F128GQ64-A	128	32	Yes	Yes	50	QFP64	-40 to +85°C
EFM32TG11B520F128IM64-A	128	32	Yes	Yes	53	QFN64	-40 to +125°C
EFM32TG11B520F128IQ64-A	128	32	Yes	Yes	50	QFP64	-40 to +125°C
EFM32TG11B540F64GM64-A	64	32	Yes	Yes	53	QFN64	-40 to +85°C
EFM32TG11B540F64GQ64-A	64	32	Yes	Yes	50	QFP64	-40 to +85°C
EFM32TG11B540F64IM64-A	64	32	Yes	Yes	53	QFN64	-40 to +125°C
EFM32TG11B540F64IQ64-A	64	32	Yes	Yes	50	QFP64	-40 to +125°C
EFM32TG11B520F128GQ48-A	128	32	Yes	Yes	34	QFP48	-40 to +85°C
EFM32TG11B520F128IQ48-A	128	32	Yes	Yes	34	QFP48	-40 to +125°C
EFM32TG11B540F64GQ48-A	64	32	Yes	Yes	34	QFP48	-40 to +85°C
EFM32TG11B540F64IQ48-A	64	32	Yes	Yes	34	QFP48	-40 to +125°C
EFM32TG11B520F128GM32-A	128	32	Yes	Yes	22	QFN32	-40 to +85°C
EFM32TG11B520F128IM32-A	128	32	Yes	Yes	22	QFN32	-40 to +125°C
EFM32TG11B540F64GM32-A	64	32	Yes	Yes	22	QFN32	-40 to +85°C
EFM32TG11B540F64IM32-A	64	32	Yes	Yes	22	QFN32	-40 to +125°C
EFM32TG11B320F128GM64-A	128	32	No	Yes	56	QFN64	-40 to +85°C
EFM32TG11B320F128GQ64-A	128	32	No	Yes	53	QFP64	-40 to +85°C
EFM32TG11B320F128IM64-A	128	32	No	Yes	56	QFN64	-40 to +125°C
EFM32TG11B320F128IQ64-A	128	32	No	Yes	53	QFP64	-40 to +125°C
EFM32TG11B340F64GM64-A	64	32	No	Yes	56	QFN64	-40 to +85°C
EFM32TG11B340F64GQ64-A	64	32	No	Yes	53	QFP64	-40 to +85°C
EFM32TG11B340F64IM64-A	64	32	No	Yes	56	QFN64	-40 to +125°C
EFM32TG11B340F64IQ64-A	64	32	No	Yes	53	QFP64	-40 to +125°C

### 3.8.1 Analog Port (APORT)

The Analog Port (APORT) is an analog interconnect matrix allowing access to many analog modules on a flexible selection of pins. Each APORT bus consists of analog switches connected to a common wire. Since many clients can operate differentially, buses are grouped by X/Y pairs.

### 3.8.2 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs are selected from among internal references and external pins. The tradeoff between response time and current consumption is configurable by software. Two 6-bit reference dividers allow for a wide range of internally-programmable reference sources. The ACMP can also be used to monitor the supply voltage. An interrupt can be generated when the supply falls below or rises above the programmable threshold.

### 3.8.3 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to 1 Msps. The output sample resolution is configurable and additional resolution is possible using integrated hardware for averaging over multiple samples. The ADC includes integrated voltage references and an integrated temperature sensor. Inputs are selectable from a wide range of sources, including pins configurable as either single-ended or differential.

### 3.8.4 Capacitive Sense (CSEN)

The CSEN module is a dedicated Capacitive Sensing block for implementing touch-sensitive user interface elements such as switches and sliders. The CSEN module uses a charge ramping measurement technique, which provides robust sensing even in adverse conditions including radiated noise and moisture. The module can be configured to take measurements on a single port pin or scan through multiple pins and store results to memory through DMA. Several channels can also be shorted together to measure the combined capacitance or implement wake-on-touch from very low energy modes. Hardware includes a digital accumulator and an averaging filter, as well as digital threshold comparators to reduce software overhead.

### 3.8.5 Digital to Analog Converter (VDAC)

The Digital to Analog Converter (VDAC) can convert a digital value to an analog output voltage. The VDAC is a fully differential, 500 ksp/s, 12-bit converter. The opamps are used in conjunction with the VDAC, to provide output buffering. One opamp is used per single-ended channel, or two opamps are used to provide differential outputs. The VDAC may be used for a number of different applications such as sensor interfaces or sound output. The VDAC can generate high-resolution analog signals while the MCU is operating at low frequencies and with low total power consumption. Using DMA and a timer, the VDAC can be used to generate waveforms without any CPU intervention. The VDAC is available in all energy modes down to and including EM3.

### 3.8.6 Operational Amplifiers

The opamps are low power amplifiers with a high degree of flexibility targeting a wide variety of standard opamp application areas, and are available down to EM3. With flexible built-in programming for gain and interconnection they can be configured to support multiple common opamp functions. All pins are also available externally for filter configurations. Each opamp has a rail to rail input and a rail to rail output. They can be used in conjunction with the VDAC module or in stand-alone configurations. The opamps save energy, PCB space, and cost as compared with standalone opamps because they are integrated on-chip.

### 3.8.7 Liquid Crystal Display Driver (LCD)

The LCD driver is capable of driving a segmented LCD display with up to 8x32 segments. A voltage boost function enables it to provide the LCD display with higher voltage than the supply voltage for the device. A patented charge redistribution driver can reduce the LCD module supply current by up to 40%. In addition, an animation feature can run custom animations on the LCD display without any CPU intervention. The LCD driver can also remain active even in Energy Mode 2 and provides a Frame Counter interrupt that can wake-up the device on a regular basis for updating data.

## 3.9 Reset Management Unit (RMU)

The RMU is responsible for handling reset of the EFM32TG11. A wide range of reset sources are available, including several power supply monitors, pin reset, software controlled reset, core lockup reset, and watchdog reset.

#### 4.1.4 DC-DC Converter

Test conditions: L\_DCDC=4.7  $\mu$ H (Murata LQH3NPN4R7MM0L), C\_DCDC=4.7  $\mu$ F (Samsung CL10B475KQ8NQNC), V\_DCDC\_I=3.3 V, V\_DCDC\_O=1.8 V, I\_DCDC\_LOAD=50 mA, Heavy Drive configuration, F\_DCDC\_LN=7 MHz, unless otherwise indicated.

**Table 4.4. DC-DC Converter**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Input voltage range	V <sub>DCDC_I</sub>	Bypass mode, I <sub>DCDC_LOAD</sub> = 50 mA	1.8	—	V <sub>VREGVDD_MAX</sub>	V
		Low noise (LN) mode, 1.8 V output, I <sub>DCDC_LOAD</sub> = 100 mA, or Low power (LP) mode, 1.8 V output, I <sub>DCDC_LOAD</sub> = 10 mA	2.4	—	V <sub>VREGVDD_MAX</sub>	V
		Low noise (LN) mode, 1.8 V output, I <sub>DCDC_LOAD</sub> = 200 mA	2.6	—	V <sub>VREGVDD_MAX</sub>	V
Output voltage programmable range <sup>1</sup>	V <sub>DCDC_O</sub>		1.8	—	V <sub>VREGVDD</sub>	V
Regulation DC accuracy	ACC <sub>DC</sub>	Low Noise (LN) mode, 1.8 V target output	TBD	—	TBD	V
Regulation window <sup>4</sup>	WIN <sub>REG</sub>	Low Power (LP) mode, LPCMPBIASEMxx <sup>3</sup> = 0, 1.8 V target output, I <sub>DCDC_LOAD</sub> ≤ 75 $\mu$ A	TBD	—	TBD	V
		Low Power (LP) mode, LPCMPBIASEMxx <sup>3</sup> = 3, 1.8 V target output, I <sub>DCDC_LOAD</sub> ≤ 10 mA	TBD	—	TBD	V
Steady-state output ripple	V <sub>R</sub>		—	3	—	mVpp
Output voltage under/overshoot	V <sub>OV</sub>	CCM Mode (LNFORCECCM <sup>3</sup> = 1), Load changes between 0 mA and 100 mA	—	25	TBD	mV
		DCM Mode (LNFORCECCM <sup>3</sup> = 0), Load changes between 0 mA and 10 mA	—	45	TBD	mV
		Overshoot during LP to LN CCM/DCM mode transitions compared to DC level in LN mode	—	200	—	mV
		Undershoot during BYP/LP to LN CCM (LNFORCECCM <sup>3</sup> = 1) mode transitions compared to DC level in LN mode	—	40	—	mV
		Undershoot during BYP/LP to LN DCM (LNFORCECCM <sup>3</sup> = 0) mode transitions compared to DC level in LN mode	—	100	—	mV
DC line regulation	V <sub>REG</sub>	Input changes between V <sub>VREGVDD_MAX</sub> and 2.4 V	—	0.1	—	%
DC load regulation	I <sub>REG</sub>	Load changes between 0 mA and 100 mA in CCM mode	—	0.1	—	%

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Max load current	I <sub>LOAD_MAX</sub>	Low noise (LN) mode, Heavy Drive <sup>2</sup> , T ≤ 85 °C	—	—	200	mA
		Low noise (LN) mode, Heavy Drive <sup>2</sup> , T > 85 °C	—	—	100	mA
		Low noise (LN) mode, Medium Drive <sup>2</sup>	—	—	100	mA
		Low noise (LN) mode, Light Drive <sup>2</sup>	—	—	50	mA
		Low power (LP) mode, LPCMPBIASEMxx <sup>3</sup> = 0	—	—	75	μA
		Low power (LP) mode, LPCMPBIASEMxx <sup>3</sup> = 3	—	—	10	mA
DCDC nominal output capacitor <sup>5</sup>	C <sub>DCDC</sub>	25% tolerance	1	4.7	4.7	μF
DCDC nominal output inductor	L <sub>DCDC</sub>	20% tolerance	4.7	4.7	4.7	μH
Resistance in Bypass mode	R <sub>BYP</sub>		—	1.2	TBD	Ω

**Note:**

1. Due to internal dropout, the DC-DC output will never be able to reach its input voltage, V<sub>VREGVDD</sub>.
2. Drive levels are defined by configuration of the PFETCNT and NFETCNT registers. Light Drive: PFETCNT=NFETCNT=3; Medium Drive: PFETCNT=NFETCNT=7; Heavy Drive: PFETCNT=NFETCNT=15.
3. LPCMPBIASEMxx refers to either LPCMPBIASEM234H in the EMU\_DCDCMISCCTRL register or LPCMPBIASEM01 in the EMU\_DCDCLOEM01CFG register, depending on the energy mode.
4. LP mode controller is a hysteretic controller that maintains the output voltage within the specified limits.
5. Output voltage under/over-shoot and regulation are specified with C<sub>DCDC</sub> 4.7 μF. Different settings for DCDCLNCOMPCTRL must be used if C<sub>DCDC</sub> is lower than 4.7 μF. See Application Note AN0948 for details.

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Current consumption in EM4H mode, with voltage scaling enabled	I <sub>EM4H_VS</sub>	128 byte RAM retention, RTCC running from LFXO	—	0.82	—	μA
		128 byte RAM retention, CRYO-TIMER running from ULFRCO	—	0.45	—	μA
		128 byte RAM retention, no RTCC	—	0.45	TBD	μA
Current consumption in EM4S mode	I <sub>EM4S</sub>	No RAM retention, no RTCC	—	0.07	TBD	μA
Current consumption of peripheral power domain 1, with voltage scaling enabled	I <sub>PD1_VS</sub>	Additional current consumption in EM2/3 when any peripherals on power domain 1 are enabled <sup>1</sup>	—	0.18	—	μA
Current consumption of peripheral power domain 2, with voltage scaling enabled	I <sub>PD2_VS</sub>	Additional current consumption in EM2/3 when any peripherals on power domain 2 are enabled <sup>1</sup>	—	0.18	—	μA

**Note:**

1. Extra current consumed by power domain. Does not include current associated with the enabled peripherals. See [3.2.3 EM2 and EM3 Power Domains](#) for a list of the peripherals in each power domain.
2. CMU\_LFRCOCTRL\_ENVREF = 1, CMU\_LFRCOCTRL\_VREFUPDATE = 1

## 4.1.9 Oscillators

### 4.1.9.1 Low-Frequency Crystal Oscillator (LFXO)

Table 4.11. Low-Frequency Crystal Oscillator (LFXO)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Crystal frequency	$f_{LFXO}$		—	32.768	—	kHz
Supported crystal equivalent series resistance (ESR)	$ESR_{LFXO}$		—	—	70	k $\Omega$
Supported range of crystal load capacitance <sup>1</sup>	$C_{LFXO\_CL}$		6	—	18	pF
On-chip tuning cap range <sup>2</sup>	$C_{LFXO\_T}$	On each of LFX TAL_N and LFX TAL_P pins	8	—	40	pF
On-chip tuning cap step size	$SS_{LFXO}$		—	0.25	—	pF
Current consumption after startup <sup>3</sup>	$I_{LFXO}$	ESR = 70 k $\Omega$ m, $C_L$ = 7 pF, GAIN <sup>4</sup> = 2, AGC <sup>4</sup> = 1	—	273	—	nA
Start- up time	$t_{LFXO}$	ESR = 70 k $\Omega$ m, $C_L$ = 7 pF, GAIN <sup>4</sup> = 2	—	308	—	ms

**Note:**

1. Total load capacitance as seen by the crystal.
2. The effective load capacitance seen by the crystal will be  $C_{LFXO\_T} / 2$ . This is because each XTAL pin has a tuning cap and the two caps will be seen in series by the crystal.
3. Block is supplied by AVDD if ANASW = 0, or DVDD if ANASW=1 in EMU\_PWRCTRL register.
4. In CMU\_LFXOCTRL register.

#### 4.1.9.2 High-Frequency Crystal Oscillator (HFXO)

Table 4.12. High-Frequency Crystal Oscillator (HFXO)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Crystal frequency	$f_{\text{HFXO}}$		4	—	48	MHz
Supported crystal equivalent series resistance (ESR)	$\text{ESR}_{\text{HFXO}}$	48 MHz crystal	—	—	50	$\Omega$
		24 MHz crystal	—	—	150	$\Omega$
		4 MHz crystal	—	—	180	$\Omega$
Supported range of crystal load capacitance <sup>1</sup>	$C_{\text{HFXO\_CL}}$		TBD	—	TBD	pF
Nominal on-chip tuning cap range <sup>2</sup>	$C_{\text{HFXO\_T}}$	On each of HFXTAL_N and HFXTAL_P pins	8.7	—	51.7	pF
On-chip tuning capacitance step	$\text{SS}_{\text{HFXO}}$		—	0.08	—	pF
Startup time	$t_{\text{HFXO}}$	48 MHz crystal, ESR = 50 Ohm, $C_L = 8$ pF	—	350	—	$\mu\text{s}$
		24 MHz crystal, ESR = 150 Ohm, $C_L = 6$ pF	—	700	—	$\mu\text{s}$
		4 MHz crystal, ESR = 180 Ohm, $C_L = 18$ pF	—	3	—	ms
Current consumption after startup	$I_{\text{HFXO}}$	48 MHz crystal	—	880	—	$\mu\text{A}$
		24 MHz crystal	—	420	—	$\mu\text{A}$
		4 MHz crystal	—	80	—	$\mu\text{A}$

**Note:**

1. Total load capacitance as seen by the crystal.
2. The effective load capacitance seen by the crystal will be  $C_{\text{HFXO\_T}}/2$ . This is because each XTAL pin has a tuning cap and the two caps will be seen in series by the crystal.



### 4.1.9.3 Low-Frequency RC Oscillator (LFRCO)

**Table 4.13. Low-Frequency RC Oscillator (LFRCO)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Oscillation frequency	f <sub>LFRCO</sub>	ENVREF <sup>2</sup> = 1	TBD	32.768	TBD	kHz
		ENVREF <sup>2</sup> = 1, T > 85 °C	TBD	32.768	TBD	kHz
		ENVREF <sup>2</sup> = 0	TBD	32.768	TBD	kHz
Startup time	t <sub>LFRCO</sub>		—	500	—	μs
Current consumption <sup>1</sup>	I <sub>LFRCO</sub>	ENVREF = 1 in CMU_LFRCOCTRL	—	370	—	nA
		ENVREF = 0 in CMU_LFRCOCTRL	—	520	—	nA

**Note:**

1. Block is supplied by AVDD if ANASW = 0, or DVDD if ANASW=1 in EMU\_PWRCTRL register.

2. In CMU\_LFRCOCTRL register.

#### 4.1.9.4 High-Frequency RC Oscillator (HFRCO)

Table 4.14. High-Frequency RC Oscillator (HFRCO)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Frequency accuracy	$f_{\text{HFRCO\_ACC}}$	At production calibrated frequencies, across supply voltage and temperature	TBD	—	TBD	%
Start-up time	$t_{\text{HFRCO}}$	$f_{\text{HFRCO}} \geq 19 \text{ MHz}$	—	300	—	ns
		$4 < f_{\text{HFRCO}} < 19 \text{ MHz}$	—	1	—	$\mu\text{s}$
		$f_{\text{HFRCO}} \leq 4 \text{ MHz}$	—	2.5	—	$\mu\text{s}$
Current consumption on all supplies	$I_{\text{HFRCO}}$	$f_{\text{HFRCO}} = 48 \text{ MHz}$	—	258	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 38 \text{ MHz}$	—	218	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 32 \text{ MHz}$	—	182	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 26 \text{ MHz}$	—	156	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 19 \text{ MHz}$	—	130	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 16 \text{ MHz}$	—	112	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 13 \text{ MHz}$	—	101	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 7 \text{ MHz}$	—	80	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 4 \text{ MHz}$	—	29	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 2 \text{ MHz}$	—	26	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 1 \text{ MHz}$	—	24	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 40 \text{ MHz, DPLL enabled}$	—	393	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 32 \text{ MHz, DPLL enabled}$	—	313	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 16 \text{ MHz, DPLL enabled}$	—	180	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 4 \text{ MHz, DPLL enabled}$	—	46	TBD	$\mu\text{A}$
		$f_{\text{HFRCO}} = 1 \text{ MHz, DPLL enabled}$	—	33	TBD	$\mu\text{A}$
Coarse trim step size (% of period)	$SS_{\text{HFRCO\_COARSE}}$		—	0.8	—	%
Fine trim step size (% of period)	$SS_{\text{HFRCO\_FINE}}$		—	0.1	—	%
Period jitter	$PJ_{\text{HFRCO}}$		—	0.2	—	% RMS

#### 4.1.11 General-Purpose I/O (GPIO)

Table 4.18. General-Purpose I/O (GPIO)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Input low voltage	$V_{IL}$	GPIO pins	—	—	$IOVDD \cdot 0.3$	V
Input high voltage	$V_{IH}$	GPIO pins	$IOVDD \cdot 0.7$	—	—	V
Output high voltage relative to IOVDD	$V_{OH}$	Sourcing 3 mA, $IOVDD \geq 3$ V, DRIVESTRENGTH <sup>1</sup> = WEAK	$IOVDD \cdot 0.8$	—	—	V
		Sourcing 1.2 mA, $IOVDD \geq 1.62$ V, DRIVESTRENGTH <sup>1</sup> = WEAK	$IOVDD \cdot 0.6$	—	—	V
		Sourcing 20 mA, $IOVDD \geq 3$ V, DRIVESTRENGTH <sup>1</sup> = STRONG	$IOVDD \cdot 0.8$	—	—	V
		Sourcing 8 mA, $IOVDD \geq 1.62$ V, DRIVESTRENGTH <sup>1</sup> = STRONG	$IOVDD \cdot 0.6$	—	—	V
Output low voltage relative to IOVDD	$V_{OL}$	Sinking 3 mA, $IOVDD \geq 3$ V, DRIVESTRENGTH <sup>1</sup> = WEAK	—	—	$IOVDD \cdot 0.2$	V
		Sinking 1.2 mA, $IOVDD \geq 1.62$ V, DRIVESTRENGTH <sup>1</sup> = WEAK	—	—	$IOVDD \cdot 0.4$	V
		Sinking 20 mA, $IOVDD \geq 3$ V, DRIVESTRENGTH <sup>1</sup> = STRONG	—	—	$IOVDD \cdot 0.2$	V
		Sinking 8 mA, $IOVDD \geq 1.62$ V, DRIVESTRENGTH <sup>1</sup> = STRONG	—	—	$IOVDD \cdot 0.4$	V
Input leakage current	$I_{IOLEAK}$	All GPIO except LFXO pins, GPIO $\leq IOVDD$ , $T \leq 85$ °C	—	0.1	TBD	nA
		LFXO Pins, GPIO $\leq IOVDD$ , $T \leq 85$ °C	—	0.1	TBD	nA
		All GPIO except LFXO pins, GPIO $\leq IOVDD$ , $T > 85$ °C	—	—	TBD	nA
		LFXO Pins, GPIO $\leq IOVDD$ , $T > 85$ °C	—	—	TBD	nA
Input leakage current on 5VTOL pads above IOVDD	$I_{5VTOLLEAK}$	$IOVDD < GPIO \leq IOVDD + 2$ V	—	3.3	TBD	$\mu$ A
I/O pin pull-up/pull-down resistor	$R_{PUD}$		TBD	40	TBD	k $\Omega$
Pulse width of pulses removed by the glitch suppression filter	$t_{IOGLITCH}$		TBD	25	TBD	ns

#### 4.1.12 Voltage Monitor (VMON)

**Table 4.19. Voltage Monitor (VMON)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Supply current (including I <sub>SENSE</sub> )	I <sub>VMON</sub>	In EM0 or EM1, 1 supply monitored, T ≤ 85 °C	—	6.3	TBD	μA
		In EM0 or EM1, 4 supplies monitored, T ≤ 85 °C	—	12.5	TBD	μA
		In EM2, EM3 or EM4, 1 supply monitored and above threshold	—	62	—	nA
		In EM2, EM3 or EM4, 1 supply monitored and below threshold	—	62	—	nA
		In EM2, EM3 or EM4, 4 supplies monitored and all above threshold	—	99	—	nA
		In EM2, EM3 or EM4, 4 supplies monitored and all below threshold	—	99	—	nA
Loading of monitored supply	I <sub>SENSE</sub>	In EM0 or EM1	—	2	—	μA
		In EM2, EM3 or EM4	—	2	—	nA
Threshold range	V <sub>VMON_RANGE</sub>		1.62	—	3.4	V
Threshold step size	N <sub>VMON_STESP</sub>	Coarse	—	200	—	mV
		Fine	—	20	—	mV
Response time	t <sub>VMON_RES</sub>	Supply drops at 1V/μs rate	—	460	—	ns
Hysteresis	V <sub>VMON_HYST</sub>		—	26	—	mV

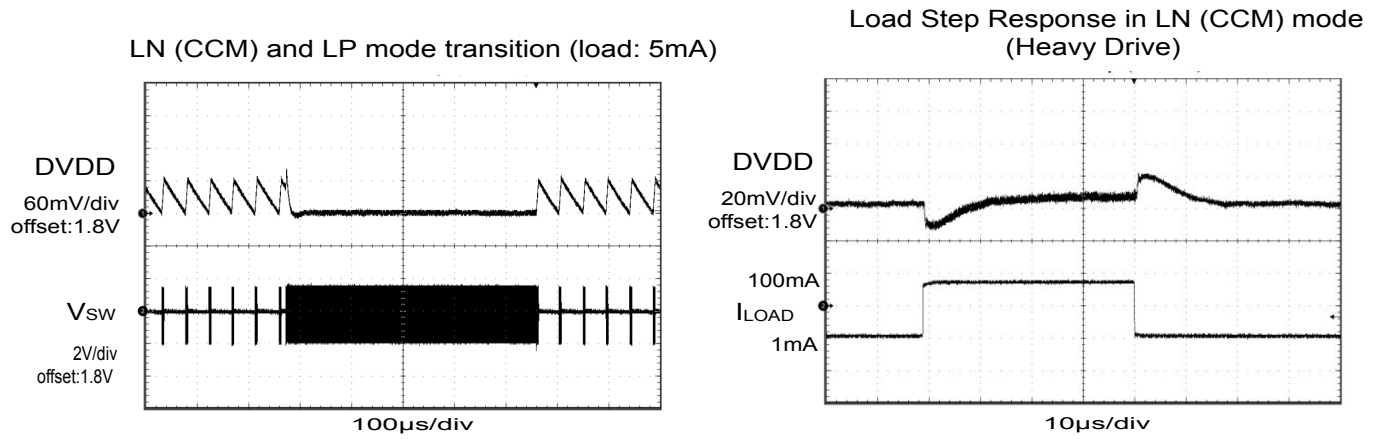


Figure 4.9. DC-DC Converter Transition Waveforms

## 5.5 EFM32TG11B1xx in QFP64 Device Pinout

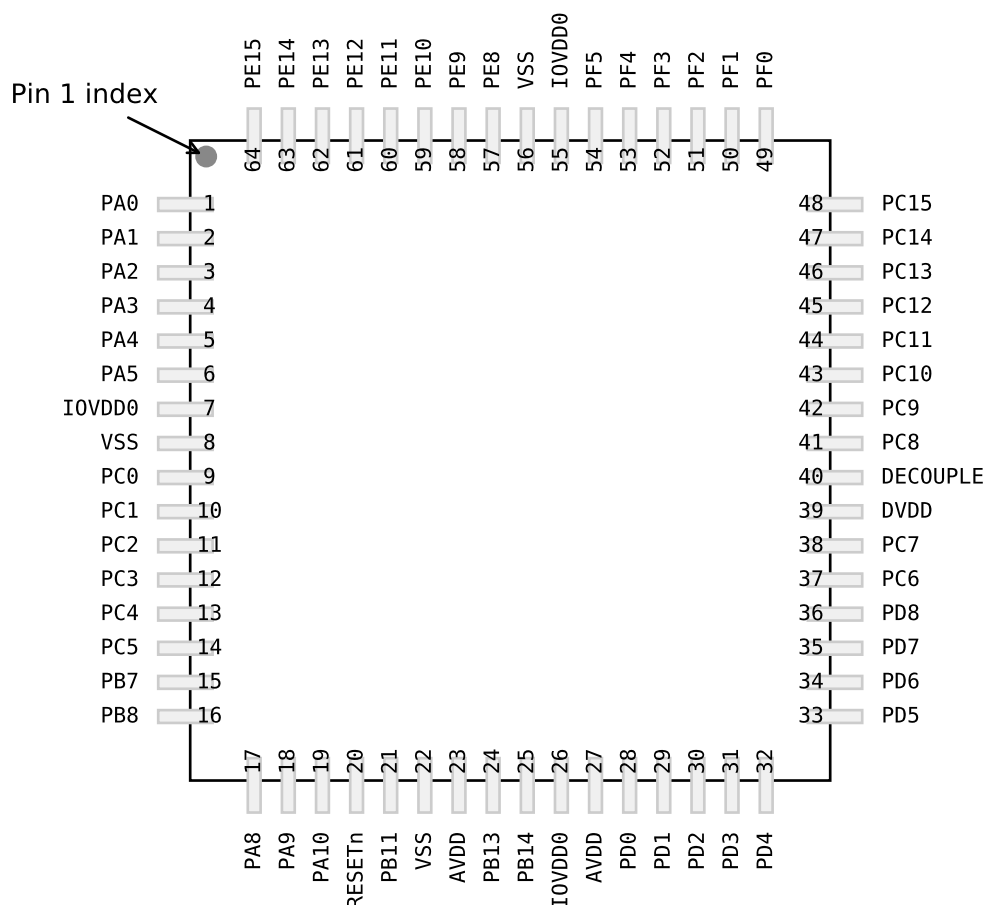


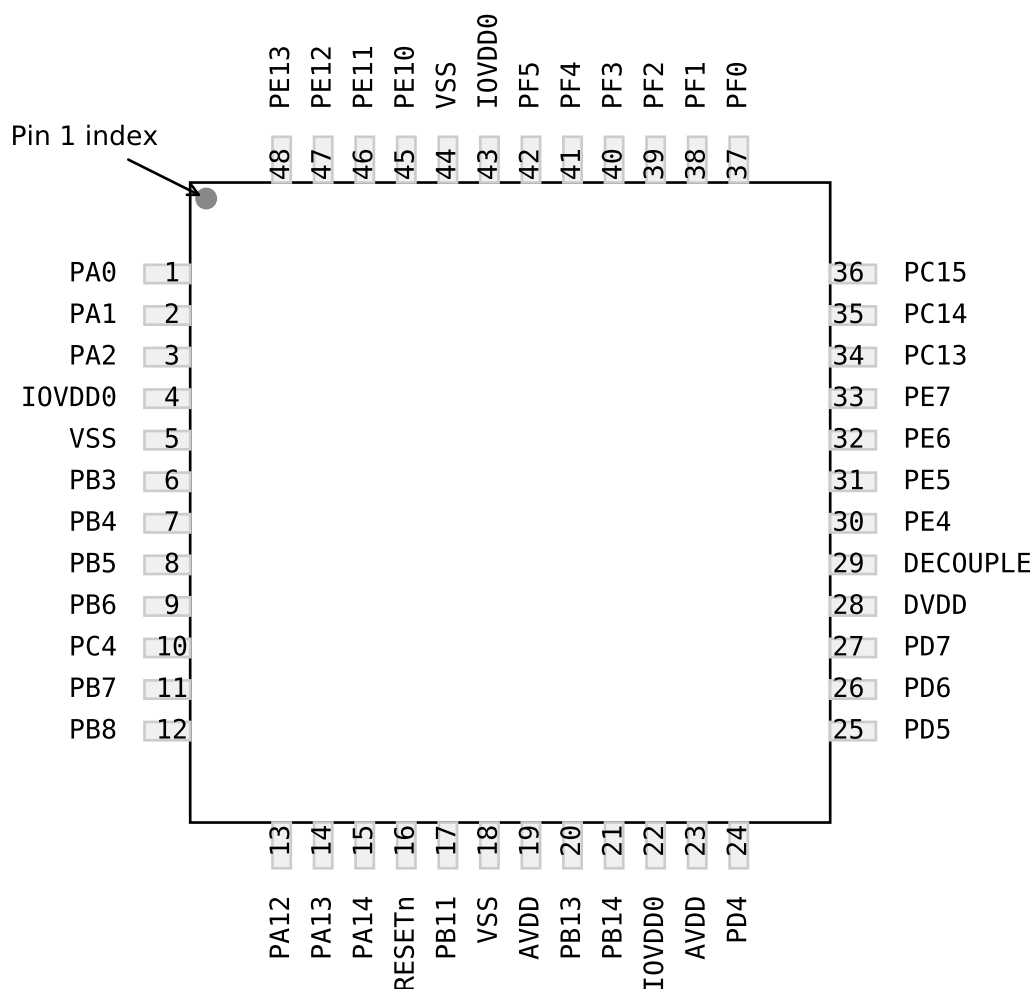
Figure 5.5. EFM32TG11B1xx in QFP64 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see [5.14 GPIO Functionality Table](#) or [5.15 Alternate Functionality Overview](#).

Table 5.5. EFM32TG11B1xx in QFP64 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PA0	1	GPIO	PA1	2	GPIO
PA2	3	GPIO	PA3	4	GPIO
PA4	5	GPIO	PA5	6	GPIO
IOVDD0	7 26 55	Digital IO power supply 0.	VSS	8 22 56	Ground
PC0	9	GPIO (5V)	PC1	10	GPIO (5V)
PC2	11	GPIO (5V)	PC3	12	GPIO (5V)

## 5.10 EFM32TG11B3xx in QFP48 Device Pinout



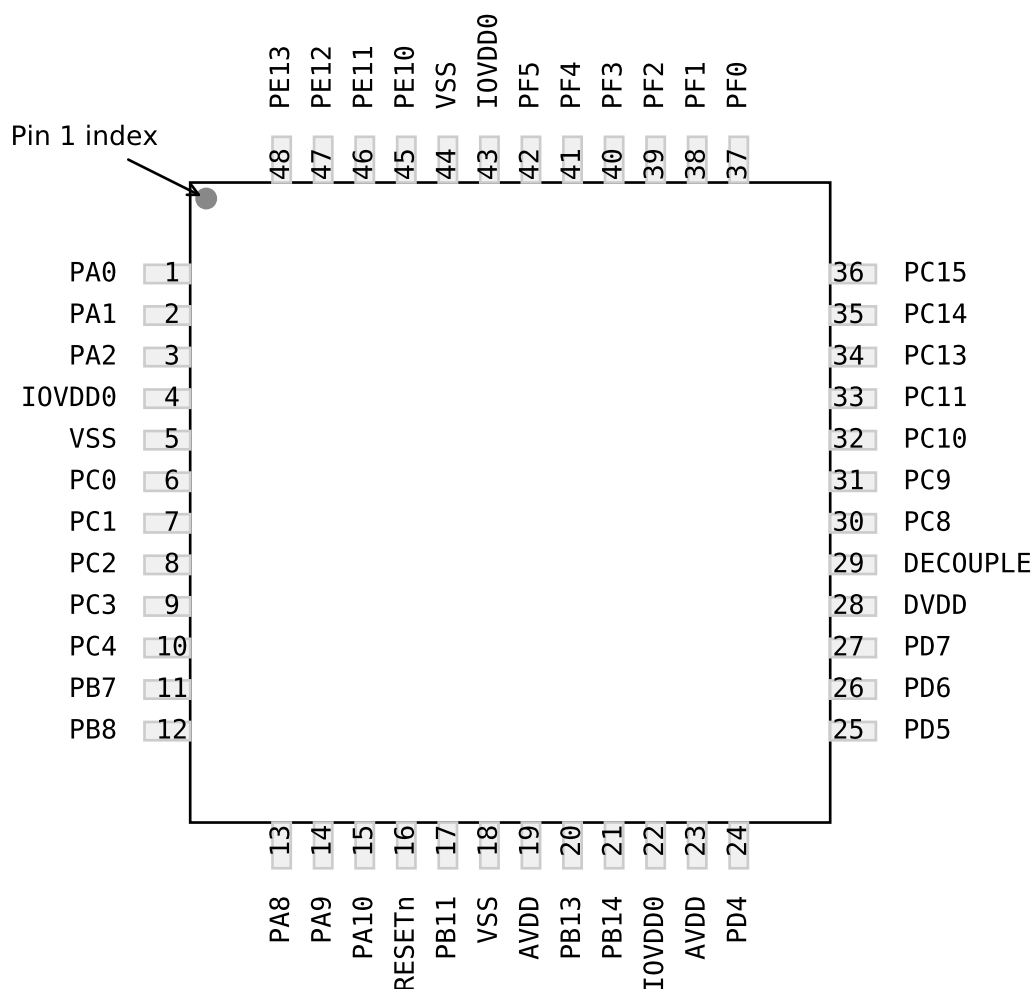
**Figure 5.10. EFM32TG11B3xx in QFP48 Device Pinout**

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see [5.14 GPIO Functionality Table](#) or [5.15 Alternate Functionality Overview](#).

**Table 5.10. EFM32TG11B3xx in QFP48 Device Pinout**

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PA0	1	GPIO	PA1	2	GPIO
PA2	3	GPIO	IOVDD0	4 22 43	Digital IO power supply 0.
VSS	5 18 44	Ground	PB3	6	GPIO
PB4	7	GPIO	PB5	8	GPIO
PB6	9	GPIO	PC4	10	GPIO

## 5.11 EFM32TG11B1xx in QFP48 Device Pinout



**Figure 5.11. EFM32TG11B1xx in QFP48 Device Pinout**

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see [5.14 GPIO Functionality Table](#) or [5.15 Alternate Functionality Overview](#).

**Table 5.11. EFM32TG11B1xx in QFP48 Device Pinout**

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PA0	1	GPIO	PA1	2	GPIO
PA2	3	GPIO	IOVDD0	4 22 43	Digital IO power supply 0.
VSS	5 18 44	Ground	PC0	6	GPIO (5V)
PC1	7	GPIO (5V)	PC2	8	GPIO (5V)
PC3	9	GPIO (5V)	PC4	10	GPIO



GPIO Name	Pin Alternate Functionality / Description			
	Analog	Timers	Communication	Other
PD5	BUSADC0Y BUSADC0X OPA2_OUT	WTIM0_CDT11 #4 WTIM1_CC3 #1	US1_RTS #1 U0_CTS #5 LEU0_RX #0 I2C1_SCL #3	
PD6	BUSADC0Y BUSADC0X ADC0_EXTP VDAC0_EXT OPA1_P	TIM1_CC0 #4 WTIM0_CDT12 #4 WTIM1_CC0 #2 LE- TIM0_OUT0 #0 PCNT0_S0IN #3	US0_RTS #5 US1_RX #2 US2_CTS #5 US3_CTS #2 U0_RTS #5 I2C0_SDA #1	CMU_CLK2 #2 LES_AL- TEX0 PRS_CH5 #2 ACMP0_O #2
PD7	BUSADC0Y BUSADC0X ADC0_EXTN OPA1_N	TIM1_CC1 #4 WTIM1_CC1 #2 LE- TIM0_OUT1 #0 PCNT0_S1IN #3	US1_TX #2 US3_CLK #1 U0_TX #6 I2C0_SCL #1	CMU_CLK0 #2 LES_AL- TEX1 ACMP1_O #2
PD8	BU_VIN	WTIM1_CC2 #2	US2_RTS #5	CMU_CLK1 #1
PC6	BUSACMP0Y BU- SACMP0X OPA3_P LCD_SEG32	WTIM1_CC3 #2	US0_RTS #2 US1_CTS #3 I2C0_SDA #2	LES_CH6
PC7	BUSACMP0Y BU- SACMP0X OPA3_N LCD_SEG33	WTIM1_CC0 #3	US0_CTS #2 US1_RTS #3 I2C0_SCL #2	LES_CH7
PE4	BUSDY BUSCX LCD_COM0	WTIM0_CC0 #0 WTIM1_CC1 #4	US0_CS #1 US1_CS #5 US3_CS #1 U0_RX #6 I2C0_SDA #7	
PE5	BUSCY BUSDX LCD_COM1	WTIM0_CC1 #0 WTIM1_CC2 #4	US0_CLK #1 US1_CLK #6 US3_CTS #1 I2C0_SCL #7	
PE6	BUSDY BUSCX LCD_COM2	WTIM0_CC2 #0 WTIM1_CC3 #4	US0_RX #1 US3_TX #1	PRS_CH6 #2
PE7	BUSCY BUSDX LCD_COM3	WTIM1_CC0 #5	US0_TX #1 US3_RX #1	PRS_CH7 #2
PC8	BUSACMP1Y BU- SACMP1X LCD_SEG34		US0_CS #2	LES_CH8 PRS_CH4 #0
PC9	BUSACMP1Y BU- SACMP1X LCD_SEG35		US0_CLK #2	LES_CH9 PRS_CH5 #0 GPIO_EM4WU2
PC10	BUSACMP1Y BU- SACMP1X		US0_RX #2	LES_CH10
PC11	BUSACMP1Y BU- SACMP1X		US0_TX #2 I2C1_SDA #4	LES_CH11
PC12	VDAC0_OUT1ALT / OPA1_OUTALT #0 BU- SACMP1Y BUSACMP1X	TIM1_CC3 #0	US0_RTS #3 US1_CTS #4 US2_CTS #4 U0_RTS #3	CMU_CLK0 #1 LES_CH12
PC13	VDAC0_OUT1ALT / OPA1_OUTALT #1 BU- SACMP1Y BUSACMP1X	TIM0_CDT10 #1 TIM1_CC0 #0 TIM1_CC2 #4 PCNT0_S0IN #0	US0_CTS #3 US1_RTS #4 US2_RTS #4 U0_CTS #3	LES_CH13
PC14	VDAC0_OUT1ALT / OPA1_OUTALT #2 BU- SACMP1Y BUSACMP1X	TIM0_CDT11 #1 TIM1_CC1 #0 TIM1_CC3 #4 LETIM0_OUT0 #5 PCNT0_S1IN #0	US0_CS #3 US1_CS #3 US2_RTS #3 US3_CS #2 U0_TX #3 LEU0_TX #5	LES_CH14 PRS_CH0 #2

Alternate	LOCATION		
Functionality	0 - 3	4 - 7	Description
OPA3_N	0: PC7		Operational Amplifier 3 external negative input.
OPA3_OUT	0: PD1		Operational Amplifier 3 output.
OPA3_P	0: PC6		Operational Amplifier 3 external positive input.
PCNT0_S0IN	0: PC13 2: PC0 3: PD6	4: PA0 6: PB5 7: PB12	Pulse Counter PCNT0 input number 0.
PCNT0_S1IN	0: PC14 2: PC1 3: PD7	4: PA1 6: PB6 7: PB11	Pulse Counter PCNT0 input number 1.
PRS_CH0	0: PA0 1: PF3 2: PC14 3: PF2		Peripheral Reflex System PRS, channel 0.
PRS_CH1	0: PA1 1: PF4 2: PC15 3: PE12		Peripheral Reflex System PRS, channel 1.
PRS_CH2	0: PC0 1: PF5 2: PE10 3: PE13		Peripheral Reflex System PRS, channel 2.
PRS_CH3	0: PC1 1: PE8 2: PE11 3: PA0		Peripheral Reflex System PRS, channel 3.
PRS_CH4	0: PC8 2: PF1		Peripheral Reflex System PRS, channel 4.
PRS_CH5	0: PC9 2: PD6		Peripheral Reflex System PRS, channel 5.
PRS_CH6	0: PA6 1: PB14 2: PE6		Peripheral Reflex System PRS, channel 6.
PRS_CH7	0: PB13 2: PE7		Peripheral Reflex System PRS, channel 7.

## 7.2 QFN80 PCB Land Pattern

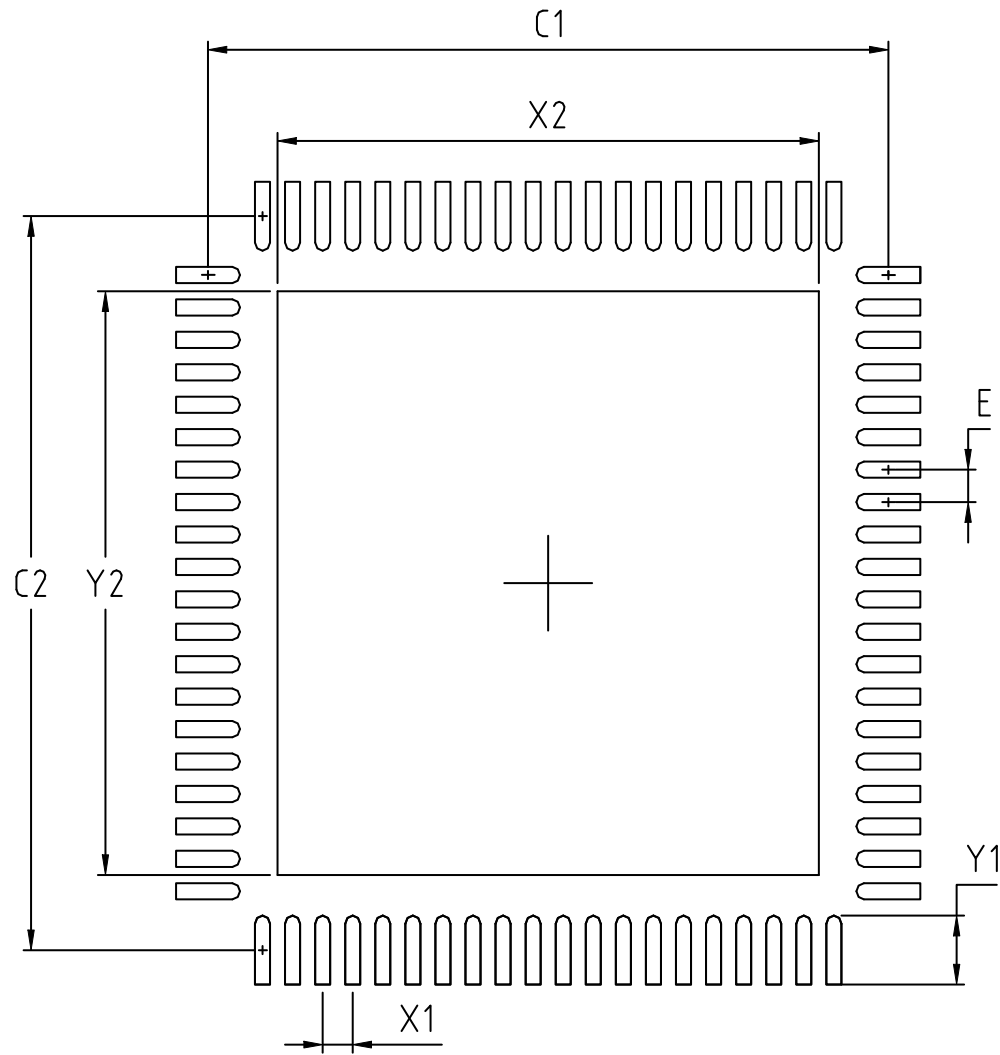


Figure 7.2. QFN80 PCB Land Pattern Drawing

### 9.3 QFN64 Package Marking



Figure 9.3. QFN64 Package Marking

The package marking consists of:

- P P P P P P P P P P – The part number designation.
- T T T T T T – A trace or manufacturing code. The first letter is the device revision.
- Y Y – The last 2 digits of the assembly year.
- W W – The 2-digit workweek when the device was assembled.

**Table 11.2. QFN32 PCB Land Pattern Dimensions**

Dimension	Typ
C1	5.00
C2	5.00
E	0.50
X1	0.30
Y1	0.80
X2	3.80
Y2	3.80

**Note:**

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. This Land Pattern Design is based on the IPC-7351 guidelines.
3. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.
4. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
5. The stencil thickness should be 0.125 mm (5 mils).
6. The ratio of stencil aperture to land pad size can be 1:1 for all perimeter pads.
7. A 2x2 array of 0.9 mm square openings on a 1.2 mm pitch should be used for the center ground pad.
8. A No-Clean, Type-3 solder paste is recommended.
9. The recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.